## Typical Applications

\author{

- Digital Communications Systems <br> - GSM and D-AMPS Systems <br> - Spread Spectrum Communication Systems <br> - GMSK, QPSK, DQPSK, QAM Modulation <br> - Image-Reject Upconverters
}


## Product Description

The RF2424 is a monolithic integrated quadrature modulator IC capable of universal direct modulation for highfrequency AM, PM, or compound carriers. Maximum output power is +7.5 dBm , which is achieved with low input I and $Q$ signal levels. This low-cost IC implements differential amplifiers for the modulation inputs, $90^{\circ}$ carrier phase shift network, carrier limiting amplifiers, two matched dou-ble-balanced mixers, summing amplifier, and an output RF amplifier which will drive $50 \Omega$ from 700 MHz to 1000 MHz .

Optimum Technology Matching ${ }^{\circledR}$ A pplied $\begin{array}{lll}\square \text { Si BJT } & \square \text { GaAs HBT } & \square \text { GaAs MESFET } \\ \square \text { Si Bi-CMOS } & \square \text { SiGe HBT } & \square \text { Si CMOS }\end{array}$


Functional Block Diagram


NOTES:

1. Shaded lead is Pin 1.
2. All dimensions are excluding mold flash.
3. Lead coplanarity - 0.005 with respect to datum "A".

Package Style: SSOP-16

## Features

- Single 2.7V to 5.5V Power Supply
- +7.5 dBm Output Power
- No Tuning Required
- Low LO Input Level
- Digitally Controlled Power Down Mode
- 700MHz to 1000 MHz Operation


## Ordering Information

| RF2424 | UHF Quadrature Modulator |
| :--- | :--- |
| RF2424 PCBA | Fully Assembled Evaluation Board |

RF2424

Absolute Maximum Ratings

| Parameter | Rating | Unit |
| :--- | :---: | :---: |
| Supply Voltage | 5.5 | $\mathrm{~V}_{\mathrm{DC}}$ |
| Input LO and RF Levels | +6.0 | dBm |
| Operating Ambient Temperature | -40 to +85 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature | -40 to +150 | ${ }^{\circ} \mathrm{C}$ |

4 Caution! ESD sensitive device.

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| Parameter | Specification |  |  | Unit | Condition |
| :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min. | Typ. | Max. |  |  |
| Carrier Input <br> Frequency Range Power Level Input impedance | $\begin{gathered} 700 \\ -6 \end{gathered}$ | 43 + j1.8 | $\begin{gathered} 1000 \\ +6 \end{gathered}$ | MHz <br> dBm <br> $\Omega$ | $\mathrm{T}=25^{\circ} \mathrm{C}, \mathrm{~V}_{\mathrm{CC}}=3 \mathrm{~V}$ <br> At 900 MHz |
| Modulation Input <br> Frequency Range Reference Voltage (VREF) Maximum Modulation (I\&Q) Gain Asymmetry Quadrature Phase Error Input DC Resistance Input Bias Current | DC | $\begin{gathered} 1.6 \\ \mathrm{~V}_{\text {REF }} \pm 0.3 \\ 0.2 \\ 1 \\ 40 \\ 40 \\ \hline \end{gathered}$ | 100 | $\begin{gathered} \mathrm{MHz} \\ \mathrm{~V} \\ \mathrm{~V} \\ \mathrm{~dB} \\ \circ \\ \mathrm{k} \Omega \\ \mu \mathrm{~A} \\ \hline \end{gathered}$ |  |
| RF Output <br> Output Power <br> Output Impedance <br> Broadband Noise Floor <br> Sideband Suppression <br> Carrier Suppression <br> $\mathrm{IM}_{3}$ Suppression | $\begin{gathered} +5.0 \\ \\ 25 \\ 25 \\ 25 \end{gathered}$ | $\begin{gathered} +7.5 \\ 50 \\ -140 \\ 35 \\ 30 \\ 30 \\ \hline \end{gathered}$ |  | $\begin{gathered} \mathrm{dBm} \\ \Omega \\ \mathrm{dBm} / \mathrm{Hz} \\ \mathrm{~dB} \\ \mathrm{~dB} \\ \mathrm{~dB} \\ \hline \end{gathered}$ | $\mathrm{V}_{\mathrm{CC}}=3 \mathrm{~V}$, LO power $=-3 \mathrm{dBm}, \mathrm{LO}$ freq $=900 \mathrm{MHz}, \mathrm{l} / \mathrm{Q}$ drive level $=0.2 \mathrm{~V}_{\mathrm{P}}$, SSB <br> DSB output (+9dBm total power) |
| Power Down <br> Turn On/Off Time <br> PD Input Resistance <br> Power Down "ON" <br> Power Down "OFF" | 10 $1.0$ | $\begin{gathered} \mathrm{V}_{\mathrm{CC}} \\ 1.2 \end{gathered}$ | 100 | $\begin{gathered} \mathrm{ns} \\ \mathrm{k} \Omega \\ \mathrm{~V} \\ \mathrm{~V} \end{gathered}$ |  |
| Power Supply <br> Voltage <br> Current <br> Power Down | 2.7 | $\begin{aligned} & 45 \\ & 53 \end{aligned}$ | $\begin{aligned} & 5.5 \\ & 55 \\ & 10 \end{aligned}$ | V <br> mA <br> mA <br> $\mu \mathrm{A}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{CC}}=3 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CC}}=5 \mathrm{~V} \end{aligned}$ |


| Pin | Function | Description | Interface Schematic |
| :---: | :---: | :---: | :---: |
| 1 | I REF | Reference voltage for the I mixer. This voltage should be the same as the DC voltage supplied to the I SIG pin. A voltage of 1.6 V is recommended. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the I SIG and I REF pins, the Q SIG and Q REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. If single ended operation is desired then the input is applied to I SIG, pin 16. In that case, I REF and Q REF are tied together and AC coupled to ground. To obtain a carrier suppression of better than 40 dB , I REF may be tuned $\pm 20 \mathrm{mV}$ relative to the I SIG. Without tuning, it will typically be better than 25 dB . |  |
| 2 | Q REF | Reference voltage for the Q mixer. This voltage should be the same as the DC voltage supplied to the Q SIG pin. A voltage of 1.6 V is recommended. The SIG and REF inputs are inputs of a differential amplifier. Therefore the REF and SIG inputs are interchangeable. If swapping the Q SIG and Q REF pins, the I SIG and I REF also need to be swapped to maintain the correct phase. It is also possible to drive the SIG and REF inputs in a balanced mode. If single ended operation is desired then the input is applied to Q SIG, pin 15. In that case, Q REF and Q REF are tied together and AC coupled to ground. To obtain a carrier suppression of better than 40 dB, Q REF may be tuned $\pm 20 \mathrm{mV}$ relative to the Q SIG. Without tuning, it will typically be better than 25 dB . |  |
| 3 | VCC1 | Power supply for the I mixer, Q mixer and the RF Output amplifier. |  |
| 4 | MIX OUT | MIXOUT: Combined output of the I mixer and Q mixer. By changing the inductor value, maximum RF output is tuned to different frequency. If the inductor value is changed, the RF output match needs to be adjusted for $50 \Omega$ output impedance. |  |
| 5 | GND1 | Ground connection for the LO and baseband amplifiers and mixers. |  |
| 6 | GND1 | Same as pin 5. |  |
| 7 | LO IN | The input of the phase shifting network. | LO O-M |
| 8 | GND3 | Ground connection for the LO phase shift network. |  |
| 9 | RF OUT | RF Output. An external LC matching network is needed for a $50 \Omega$ match. |  |
| 10 | GND2 | Ground connection for the RF output stage. |  |
| 11 | GND1 | Same as pin 5. |  |
| 12 | PD | Power Down control. When this pin is "low", all circuits are shut off. |  |
| 13 | VCC2 | Power supply for all circuits except mixers and output amplifier. |  |
| 14 | GND1 | Same as pin 5. |  |
| 15 | Q SIG | Baseband input to the Q mixer. Maximum output power is obtained when the input signal has a peak to peak amplitude of 400 mV . The DC level for this pin is 1.6 V , same as QREF. | See pin 2. |
| 16 | I SIG | Baseband input to the Q mixer. Maximum output power is obtained when the input signal has a peak to peak amplitude of 400 mV . The DC level for this pin is 1.6 V , same as QREF. | See pin 1. |

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## Application Schematic



NOTE:
The values of $R$ and $C$ depend on the minimum baseband frequency (i.e., the cutoff frequency of this high pass filter should be lower than the lowest frequency component in the I/Q spectrum).

## Evaluation Board Schematic

(Download Bill of Materials from www.rfmd.com.)


RF2424

## Evaluation Board Layout 2" x 2"



